

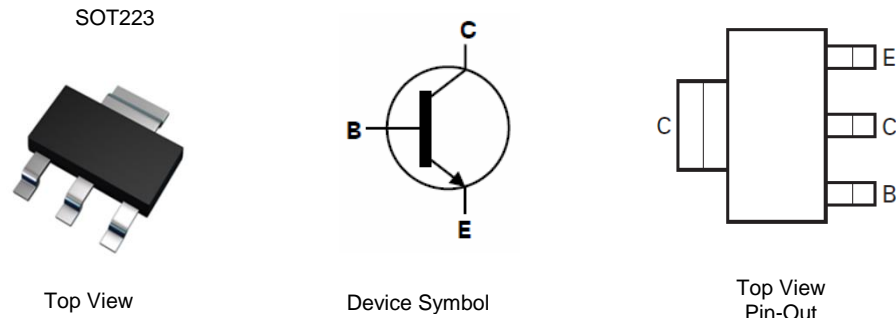
25V NPN HIGH PERFORMANCE TRANSISTOR IN SOT223

Features

- $BV_{CEO} > 25V$
- $I_C = 3A$ High Continuous Current
- $I_{CM} = 8A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < 300mV @ 1A$
- Complementary PNP Type: FZT749
- **Lead-Free Finish; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/contact-us) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 **Ⓒ3**
- Weight: 0.112 grams (Approximate)

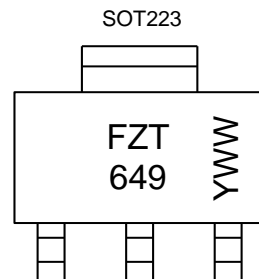


Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT649TA	Standard	FZT649	7	12	1,000
FZT649TC	Standard	FZT649	13	12	4,000

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



FZT649 = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 5= 2015)
 WW or $\bar{W}W$ = Week Code (01~53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	35	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	3	A
Peak Pulse Current	I _{CM}	8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

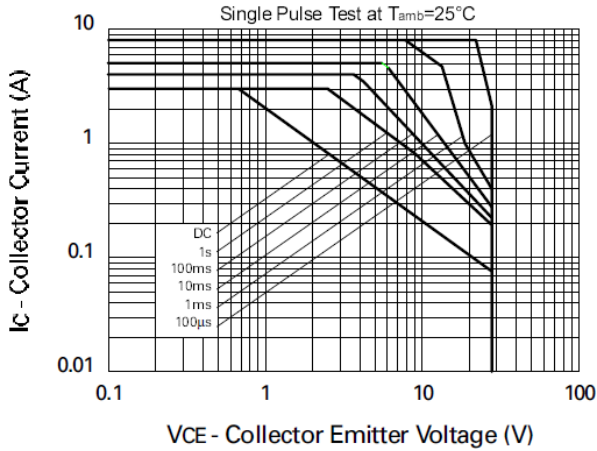
Characteristic	Symbol	Value	Unit	
Power Dissipation	P _D	(Note 5)	2	W
		(Note 6)	3	W
Thermal Resistance, Junction to Ambient	R _{θJA}	(Note 5)	62.5	°C/W
		(Note 6)	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{θJL}	12.9	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

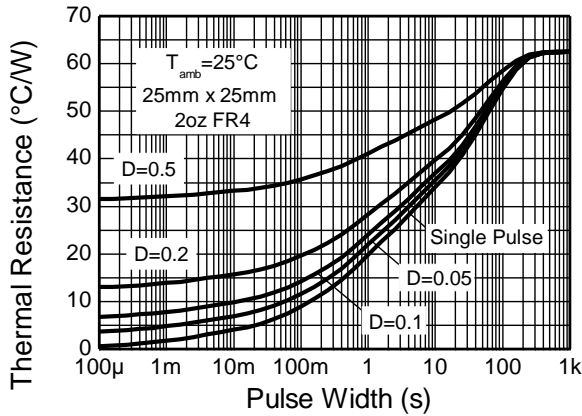
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 6. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

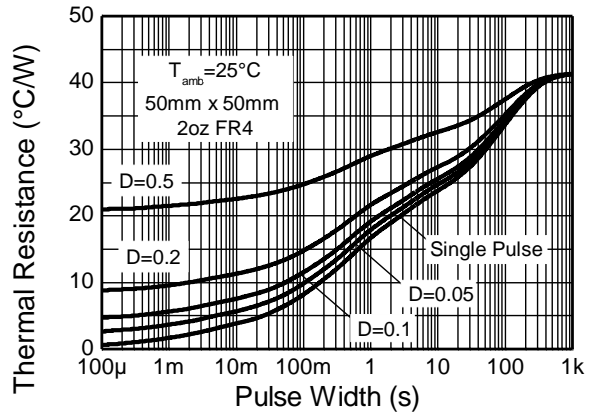
Thermal Characteristics and Derating Information



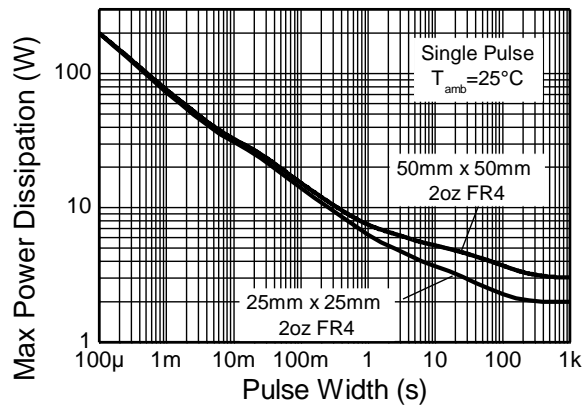
Safe Operating Area



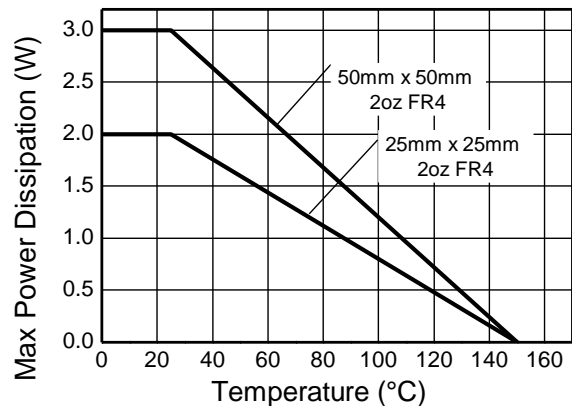
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



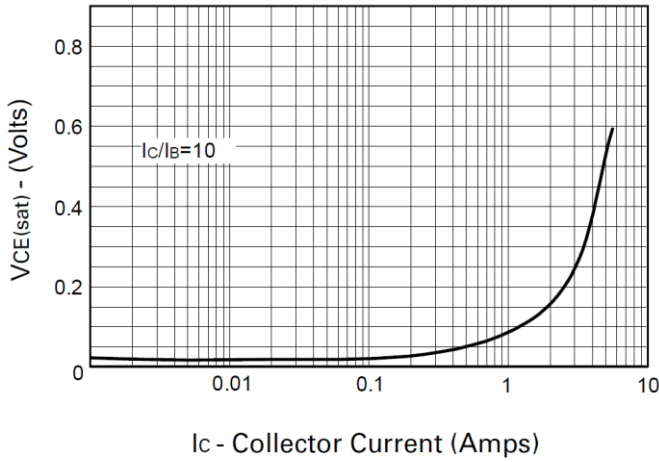
Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	35	–	–	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	25	–	–	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	–	–	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	–	–	0.1	μA	V _{CB} = 30V
		–	–	10		V _{CB} = 30V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	–	–	100	nA	V _{EB} = 4V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	–	0.12	0.3	V	I _C = 1A, I _B = 100mA
		–	0.40	0.6		I _C = 3A, I _B = 300mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	–	0.9	1.25	V	I _C = 1A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	–	0.8	1.0	V	I _C = 1A, V _{CE} = 2V
DC Current Gain (Note 9)	h _{FE}	70	200	–	–	I _C = 50mA, V _{CE} = 2V
		100	200	300		I _C = 1A, V _{CE} = 2V
		75	150	–		I _C = 2A, V _{CE} = 2V
		15	50	–		I _C = 6A, V _{CE} = 2V
Current Gain-Bandwidth Product	f _T	150	240	–	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
Switching Times	t _{on}	–	55	–	ns	I _C = 500mA, V _{CC} = 10V, I _{B1} = -I _{B2} = 50mA
	t _{off}	–	300	–		
Output Capacitance	C _{obo}	–	25	50	pF	V _{CB} = 10V, f = 1MHz

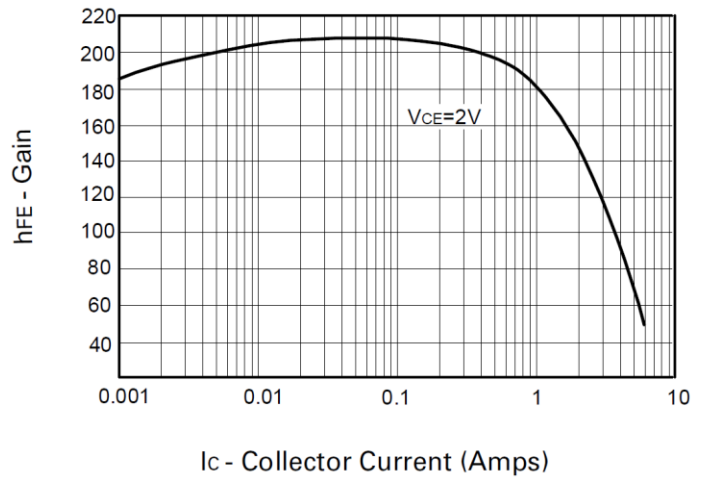
Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



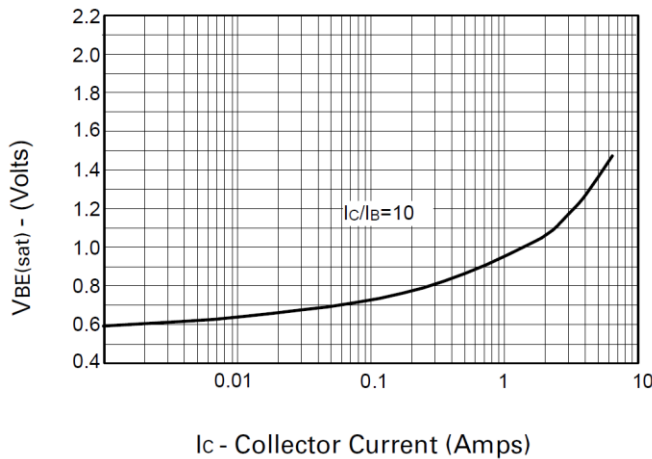
IC - Collector Current (Amps)

VCE(sat) v IC



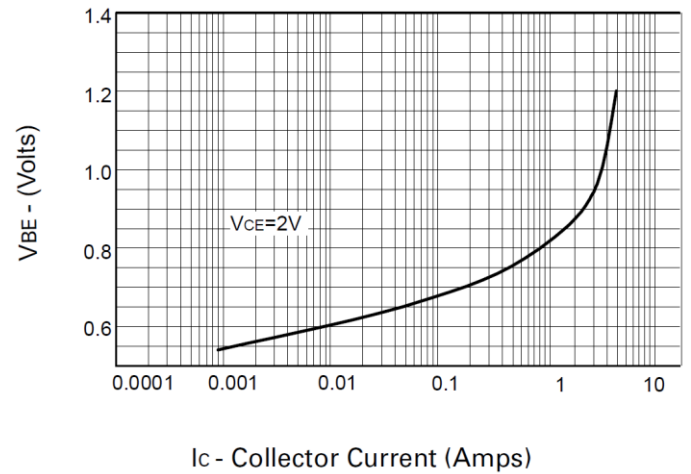
IC - Collector Current (Amps)

hFE v IC



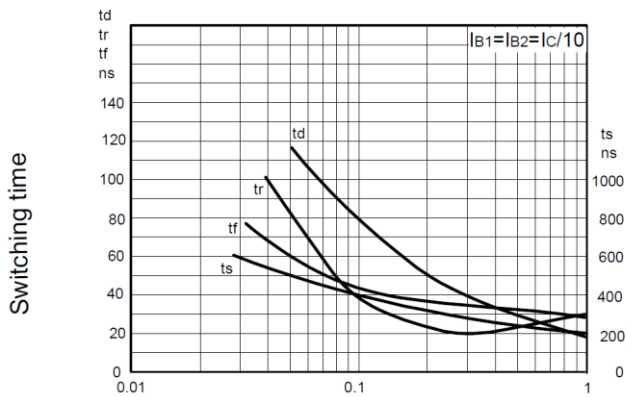
IC - Collector Current (Amps)

VBE(sat) v IC



IC - Collector Current (Amps)

VBE(on) v IC



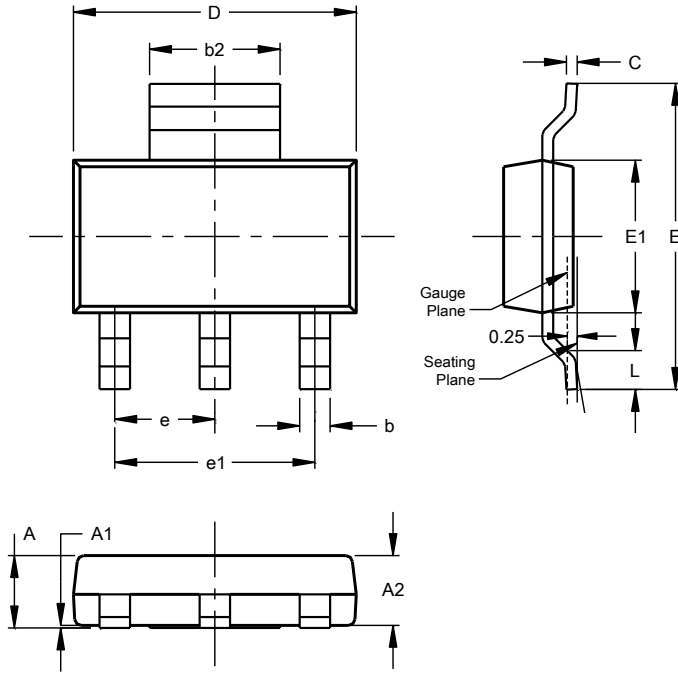
IC - Collector Current (Amps)

Switching Speeds

Package Outline Dimensions

Please see <https://www.diodes.com/design/support/packaging/> for the latest version.

SOT223 (Type DN)

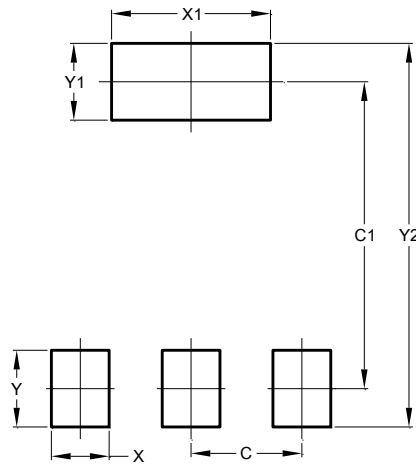


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <https://www.diodes.com/design/support/packaging/> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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